

This listing of claims will replace all prior versions and listings of claims in the application:

**Listing of Claims:**

1. (Currently amended) An anisotropic electrically conductive adhesive for semiconductor parts, comprising:

a cyclic structure-containing thermoplastic polymer selected from the group consisting of (a) a cycloolefin polymer and (b) an aromatic-condensed polymer having a repeating unit of an aromatic ring in its main chain, and having a number average molecular weight of 1,000 to 500,000, and

an electrically conductive filler,

whereby the adhesive has anisotropic electrical conductivity and wherein the cyclic structure-containing thermoplastic polymer has a functional group selected from the group consisting of an alcohol group, epoxy group, carboxyl group, acid anhydride group and silanol group.

2. (Currently amended) The adhesive for semiconductor parts according to Claim 1, wherein the cyclic structure-containing thermoplastic polymer has the a functional group in a proportion of 5 to 100 mol% based on the total number of monomer units in the polymer.

3. (Cancelled).

4. (Previously amended) The adhesive for semiconductor parts according to Claim 1, wherein the cyclic structure-containing thermoplastic polymer is at least one thermoplastic norbornene resin selected from the group consisting of (1) an addition

(co)polymer of an alicyclic monomer having a norbornene ring, (2) an addition copolymer of an alicyclic monomer having a norbornene ring and a vinyl compound, (3) a ring-opening (co)polymer of an alicyclic monomer having a norbornene ring, and (4) a hydrogenated product of the ring-opening (co)polymer of the alicyclic monomer having a norbornene ring.

5. (Previously amended) The adhesive for semiconductor parts according to Claim 1, wherein the cyclic structure-containing thermoplastic polymer is at least one selected from the group consisting of an addition polymer of a cyclic conjugated diene monomer and a hydrogenated product of the addition polymer.

6. (Previously amended) The adhesive for semiconductor parts according to Claim 1, wherein the cyclic structure-containing thermoplastic polymer is poly(phenylene ether).

7. (Cancelled).

8. (Previously amended) The adhesive for semiconductor parts according to Claim 1, wherein the amount of the conductive filler is 1 to 100 parts by weight based on 100 parts by weight of the cyclic structure-containing thermoplastic polymer.

9. (Previously amended) The adhesive for semiconductor parts according to Claim 1, wherein the filler is a micro-capsulate conductive filler.

10. (Previously amended) The adhesive for semiconductor parts according to Claim 1, further comprising a low-molecular weight resin in a proportion of 1 to 50 parts by weight per 100 parts by weight of the cyclic structure-containing thermoplastic polymer.

11. (Previously amended) The adhesive for semiconductor parts according to Claim 1 wherein the glass transition temperature of the cyclic structure-containing thermoplastic polymer is at least 100°C.

12. (Previously amended) The adhesive for semiconductor parts according to Claim 2, wherein the cyclic structure-containing thermoplastic polymer is a modified polymer obtained by graft-modifying, with a functional group-containing unsaturated compound,

a hydrogenated product of a ring-opening copolymer of tetracyclododecene or a derivative thereof,

an addition copolymer of tetracyclododecene or a derivative thereof and a vinyl compound, or

a hydrogenated product of an addition polymer of 1,3-cyclohexadiene.

13. (Cancelled).

14. (Original) The adhesive for semiconductor parts according to Claim 10, wherein the low-molecular weight resin is an epoxy resin.

15. (Previously amended) The adhesive for semiconductor parts according to Claim 10, wherein the amount of the conductive filler is 1 to 100 parts by weight based on 100 parts by weight of the cyclic structure-containing thermoplastic polymer.

16. (Previously amended) An adhesive film for semiconductor parts, which is obtained by forming a film from the adhesive according to Claim 1.

17. (Previously amended) A semiconductor part package obtained by bonding a semiconductor part to a substrate with a solution or film of the adhesive according to Claim 1.

18. (Original) A process for producing a semiconductor part package, which comprises laminating the adhesive film according to Claim 16 on the surface of a substrate, placing a semiconductor part on the adhesive film, bonding the semiconductor part to the substrate by heating and pressurizing the adhesive film at a temperature not lower than the glass transition temperature of the cyclic structure-containing thermoplastic polymer, and then cooling the adhesive film.

19. (Previously amended) A process for producing a semiconductor part package, which comprises applying a solution of the adhesive according to Claim 1 to the surface of a substrate, drying a solvent to form an adhesive layer, placing a semiconductor part on the adhesive layer, bonding the semiconductor part to the substrate by heating and pressurizing the adhesive layer at a temperature not lower than the glass transition temperature of the cyclic structure-containing thermoplastic polymer, and then cooling the adhesive layer.

20. (Previously added) A process for producing a semiconductor part package, which comprises laminating the adhesive film according to Claim 16 on the surface of a substrate having an electrode (A) thereon,

placing a semiconductor part on the adhesive film,

bonding the semiconductor part having an electrode (B) to the substrate to electrically connect the electrode (A) with the electrode (B), by heating and pressurizing the adhesive film at a temperature not lower than the glass transition temperature of the cyclic structure-containing thermoplastic polymer, and then

cooling the adhesive film.

21. (Previously added) A process for producing a semiconductor part package, which comprises

applying a solution of the adhesive according to Claim 1 on the surface of a substrate having an electrode (A) thereon,

drying a solvent from the solution to form an adhesive layer,

placing a semiconductor part on the adhesive layer,

bonding the semiconductor part having an electrode (B) to the substrate to electrically connect the electrode (A) with the electrode (B), by heating and pressurizing the adhesive layer at a temperature not lower than the glass transition temperature of the cyclic structure-containing thermoplastic polymer, and then

cooling the adhesive layer.

22. (Previously added) The adhesive for semiconductor parts according Claim 1, wherein the filler has an average particle diameter of  $(\text{length} + \text{breadth})/2$  in the range of 0.1 to 30 $\mu\text{m}$ .

23. (Previously added) The adhesive for semiconductor parts according Claim 1, wherein the filler has an average particle diameter of  $(\text{length} + \text{breadth})/2$  in the range of 1 to 20 $\mu\text{m}$ .

24. (Previously added) The adhesive for semiconductor parts according Claim 1, wherein the filler has an average particle diameter of  $(\text{length} + \text{breadth})/2$  in the range of 5 to 15 $\mu\text{m}$ .

25. (Previously added) The adhesive for semiconductor parts according Claim 1, wherein the cyclic structure-containing thermoplastic polymer has a number average molecular weight of 3,000 to 300,000.

26. (Previously added) The adhesive for semiconductor parts according Claim 1, wherein the cyclic structure-containing thermoplastic polymer has a number average molecular weight of 5,000 to 250,000.

27. (Previously added) The adhesive for semiconductor parts according Claim 1, wherein the amount of the conductive filler is 2 to 70 parts by weight based on 100 parts by weight of the cyclic structure-containing thermoplastic polymer.

28. (Previously added) The adhesive for semiconductor parts according Claim 1, wherein the amount of the conductive filler is 3 to 50 parts by weight based on 100 parts by weight of the cyclic structure-containing thermoplastic polymer.

29. (Previously added) The adhesive film according to Claim 16, which has a thickness of about 1  $\mu\text{m}$  to 1 mm.